

FDC3612

N-Channel PowerTrench® MOSFET 100V 2.6A, 125mΩ

Product Overview

For complete documentation, see the data sheet.

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low RDS(ON) and fast switching speed.

Features

- 2.6 A, 100 V
- RDS(on) = 125 mΩ @ VGS = 10 V
- RDS(on) = 135 mΩ @ VGS = 6 V
- High performance trench technology for extremely low RDS(ON)
- Low gate charge (14nC typical)
- High power and current handling capability
- Fast switching speed

Applications

- This product is general usage and suitable for many different applications.

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	V _{DS(BR) Min} (V)	V _{GS Max} (V)	V _{GS(th) Max} (V)	I _{D Max} (A)	P _{D Max} (W)	R _{DS(on) Max @ V_{GS} = 2.5 V} (mΩ)	R _{DS(on) Max @ V_{GS} = 4.5 V} (mΩ)	R _{DS(on) Max @ V_{GS} = 10 V} (mΩ)	Q _{g Typ @ V_{GS} = 4.5 V} (nC)	Q _{g Typ @ V_{GS} = 10 V} (nC)	C _{iss Typ} (pF)	Package Type
FDC3612	0.2379		Active	N-Channel	Single	100	±20	4	2.6	1.6	-	-	125	-	14	660	TSO T-23-6